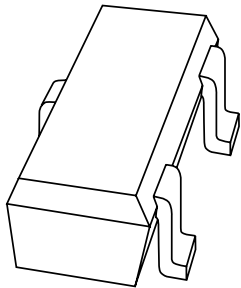


# DATA SHEET



**2PB709AW**

**PNP general purpose transistor**

Product specification

2002 Jun 26

# PNP general purpose transistor

# 2PB709AW

### FEATURES

- High collector current (max. 100 mA)
- Low collector-emitter saturation voltage (max. 500 mV).

### APPLICATIONS

- General purpose switching and amplification.

### DESCRIPTION

PNP transistor in an SC-70 (SOT323) plastic package.  
NPN complement: 2PD601AW

### MARKING

| TYPE NUMBER | MARKING CODE <sup>(1)</sup> |
|-------------|-----------------------------|
| 2PB709AQW   | N5*                         |
| 2PB709ARW   | N7*                         |
| 2PB709ASW   | N9*                         |

### Note

- \* = p: made in Hong Kong.  
\* = t: made in Malaysia.

### PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | base        |
| 2   | emitter     |
| 3   | collector   |

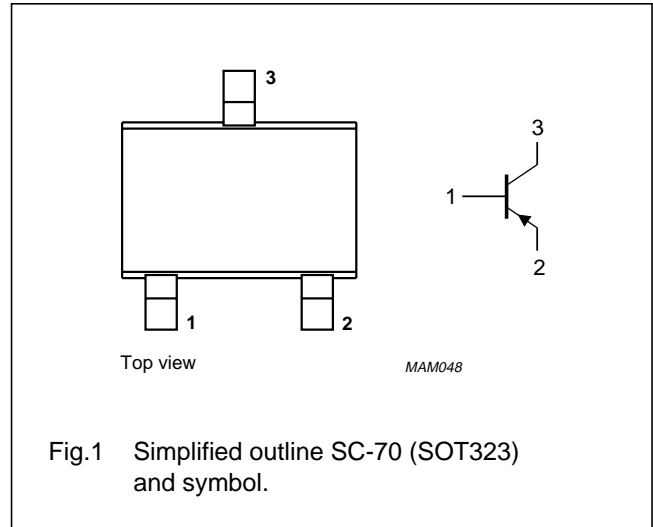


Fig.1 Simplified outline SC-70 (SOT323) and symbol.

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL           | PARAMETER                     | CONDITIONS                       | MIN. | MAX. | UNIT |
|------------------|-------------------------------|----------------------------------|------|------|------|
| V <sub>CBO</sub> | collector-base voltage        | open emitter                     | –    | –45  | V    |
| V <sub>CEO</sub> | collector-emitter voltage     | open base                        | –    | –45  | V    |
| V <sub>EBO</sub> | emitter-base voltage          | open collector                   | –    | –6   | V    |
| I <sub>C</sub>   | collector current (DC)        |                                  | –    | –100 | mA   |
| I <sub>CM</sub>  | peak collector current        |                                  | –    | –200 | mA   |
| P <sub>tot</sub> | total power dissipation       | T <sub>amb</sub> ≤ 25 °C; note 1 | –    | 200  | mW   |
| T <sub>stg</sub> | storage temperature           |                                  | –65  | +150 | °C   |
| T <sub>j</sub>   | junction temperature          |                                  | –    | 150  | °C   |
| T <sub>amb</sub> | operating ambient temperature |                                  | –65  | +150 | °C   |

### Note

1. For mounting conditions, see “Thermal considerations and footprint design for SOT323 in the General Part of Data Handbook SC18”.

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## THERMAL CHARACTERISTICS

| SYMBOL        | PARAMETER                                   | CONDITIONS | VALUE | UNIT |
|---------------|---|------------|-------|------|
| $R_{th\ j-a}$ | thermal resistance from junction to ambient | note 1     | 625   | K/W  |

## Note

- For mounting conditions, see "Thermal considerations and footprint design for SOT323 in the General Part of Data Handbook SC18".

## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

| SYMBOL      | PARAMETER   | CONDITIONS   | MIN. | MAX. | UNIT          |
|-------------|---|--|------|------|---------------|
| $I_{CBO}$   | collector-base cut-off current                              | $I_E = 0; V_{CB} = -45\text{ V}$                                     | –    | –10  | nA            |
|             |   | $I_E = 0; V_{CB} = -45\text{ V}; T_j = 150\text{ °C}$                | –    | –5   | $\mu\text{A}$ |
| $I_{EBO}$   | emitter-base cut-off current                                | $I_C = 0; V_{EB} = -5\text{ V}$                                      | –    | –10  | nA            |
| $h_{FE}$    | DC current gain<br>2PB709AQW<br>2PB709ARW<br>2PB709ASW      | $I_C = -2\text{ mA}; V_{CE} = -10\text{ V}$                          | 160  | 260  |               |
|             |   |  | 210  | 340  |               |
|             |   |  | 290  | 460  |               |
| $V_{CEsat}$ | collector-emitter saturation voltage                        | $I_C = -100\text{ mA}; I_B = -10\text{ mA};$<br>note 1               | –    | –500 | mV            |
| $C_c$       | collector capacitance                                       | $I_E = i_e = 0; V_{CB} = -10\text{ V};$<br>$f = 1\text{ MHz}$        | –    | 5    | pF            |
| $f_T$       | transition frequency<br>2PB709AQW<br>2PB709ARW<br>2PB709ASW | $I_C = -1\text{ mA}; V_{CE} = -10\text{ V};$<br>$f = 100\text{ MHz}$ | 60   | –    | MHz           |
|             |   |  | 70   | –    | MHz           |
|             |   |  | 80   | –    | MHz           |

## Note

- Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .

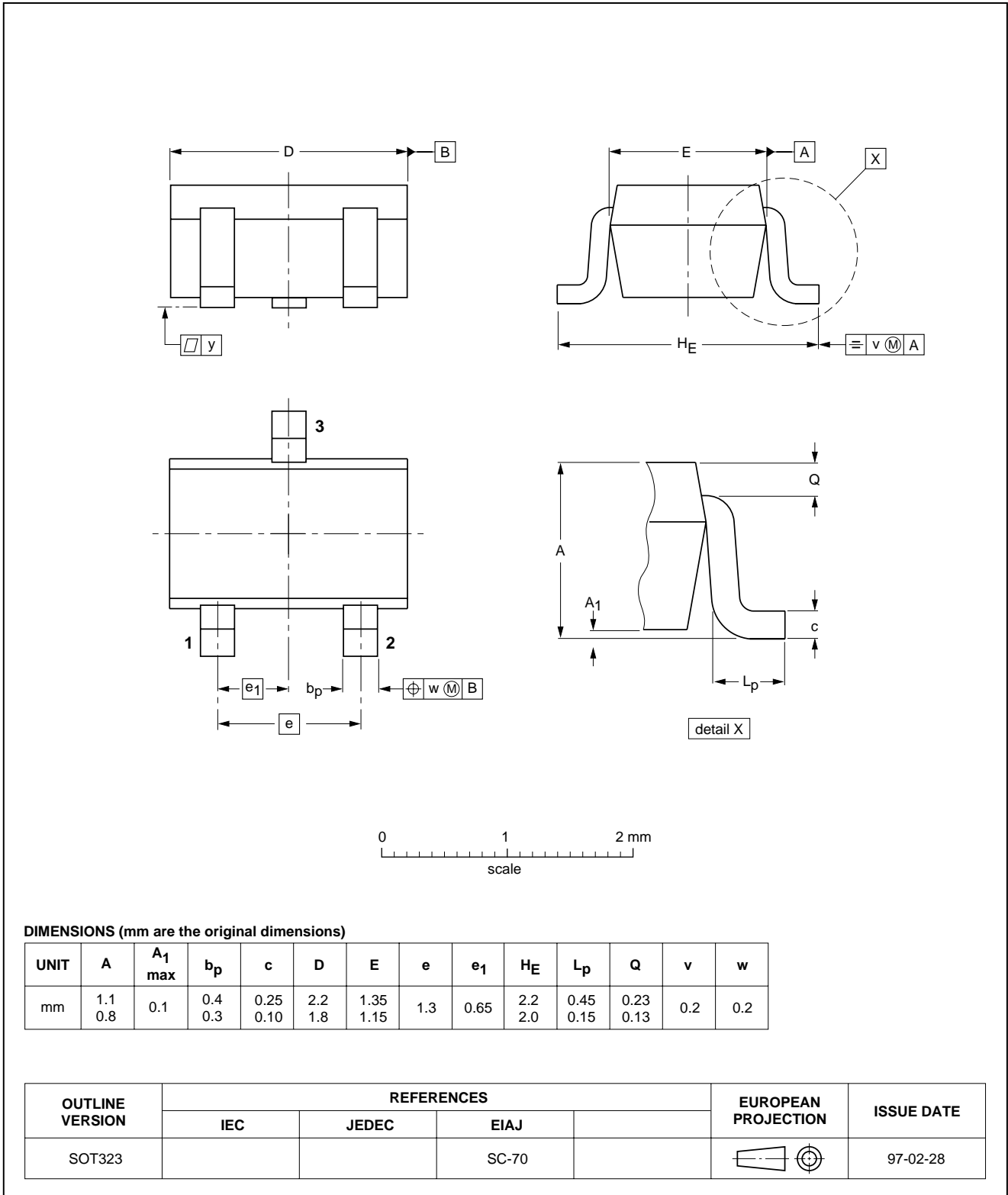
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



## PNP general purpose transistor

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## DATA SHEET STATUS

| DATA SHEET STATUS <sup>(1)</sup> | PRODUCT STATUS <sup>(2)</sup> | DEFINITIONS  |
|----------------------------------|-------------------------------|--|
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| Preliminary data                 | Qualification                 | This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.                                     |
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**NOTES**

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**NOTES**

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